

**AMENDMENTS TO THE CLAIMS**

1. **(Currently Amended)** A method for forming a semiconductor device comprising the steps of:

depositing a monoatomic ~~metal~~-film including a metal on a base by using a metal source including a compound containing said metal and no oxygen; and

depositing a metal oxide film including oxide of said metal on said monoatomic ~~metal~~ film by using a CVD technique.

2. **(Currently Amended)** The method according to claim 1, further comprising, before said monoatomic ~~metal~~-film depositing step, the step of supplying oxidizing gas onto a surface of said base.

3. **(Original)** The method according to claim 2, wherein said oxidizing gas includes heated H<sub>2</sub>O.

4. **(Original)** The method according to claim 2, wherein said oxidizing gas includes at least one gas selected from the group consisting O<sub>2</sub>, active oxygen, ozone, and N<sub>2</sub>O.

5. **(Currently Amended)** The method according claim 1, further comprising, before said monoatomic ~~metal~~-film depositing step, the step of supplying hydrofluoric acid onto a surface of said base.

6. **(Original)** The method according to claim 1, wherein said metal source includes at least one said compound selected from the group consisting of  $\text{TaCl}_5$ ,  $\text{TaF}_5$  and  $\text{Ta}(\text{N}(\text{C}_2\text{H}_5)_2)_3$ , and said metal oxide film is tantalum oxide.
7. **(Original)** The method according to claim 1, wherein said metal source includes  $\text{Al}(\text{CH}_3)_3$ , and said metal oxide is titanium oxide.
8. **(Original)** The method according to claim 1, wherein said metal source includes  $\text{TiCl}_4$  or  $\text{Ti}(\text{N}(\text{CH}_3)_2)_4$  and said metal oxide is titanium oxide.
9. **(Original)** The method according to claim 1, wherein said metal source includes at least one said compound selected from the group consisting of  $\text{Hf}(\text{NCH}_3)_2)_4$ ,  $\text{Hf}(\text{N}(\text{C}_2\text{H}_5)(\text{CH}_3))_4$  and  $\text{Hf}(\text{C}_2\text{H}_5)_2)_4$ , and said metal oxide is hafnium oxide.
10. **(Original)** The method according to claim 1, wherein said metal source includes at least one said compound selected from the group consisting of  $\text{NbCl}_5$ ,  $\text{NbF}_5$  and  $\text{Nb}(\text{N}(\text{C}_2\text{H}_5)_2)_3$ , and said metal oxide is niobium oxide.
11. **(Currently Amended)** The method according to claim 1, further comprising, between said monoatomic metal-film depositing step and said metal oxide film depositing step, the step of supplying oxidizing gas onto a surface of said monoatomic metal-film.
12. **(Currently Amended)** The method according to ~~claim 12~~claim 1, wherein said base is either silicon substrate, polysilicon film, silicon nitride film or a metallic film.

**13. (Original)** The method according to claim 1, further comprising the step of forming a conductive film on said metal oxide film, wherein said steps are used for forming a capacitor including said base as a bottom electrode, said metal oxide film as a capacitor insulation film, and said conductive film as a top electrode.

**14. (Currently Amended)** A method for forming a semiconductor device comprising:

depositing a monoatomic ~~metal~~-film including a metal on a base in an oxygen-free environment; and

depositing a metal oxide film including an oxide of the metal on the monoatomic ~~metal~~ film using a CVD technique.

**15. (Previously Presented)** The method of claim 14, wherein the semiconductor device is adapted to function as a capacitor.

**16. (Currently Amended)** The method of claim 14, wherein the depositing of the monoatomic ~~metal~~-film including the metal includes using a metal source including a compound containing the metal.

**17. (Currently Amended)** A semiconductor device formed by a method, the method comprising:

depositing a monoatomic ~~metal~~-film including a metal on a base in an oxygen-free environment; and

depositing a metal oxide film including an oxide of the metal on the monoatomic ~~metal~~ film using a CVD technique.

**18. (Previously Presented)** The semiconductor device of claim 17, wherein the semiconductor device is adapted to function as a capacitor.

**19. (New)** A method to form a semiconductor device comprising the steps of:

depositing a monoatomic seed layer containing a metal on a base by using a metal source including a compound containing said metal and no oxygen, said deposition done via an atomic layer deposition (ALD) technique; and

introducing an oxygen source to convert said monoatomic seed layer containing metal to a monoatomic seed layer containing a metal oxide and depositing a film of the same metal oxide on said monoatomic seed layer via a CVD technique.

**20. (New)** The method of claim 19, wherein said metal source includes at least one said compound selected from the group consisting of  $\text{TaCl}_5$ ,  $\text{TaF}_5$  and  $\text{Ta}(\text{N}(\text{C}_2\text{H}_5)_2)_3$ , and said metal oxide film is tantalum oxide.

**21. (New)** The method of claim 19, wherein said oxygen source is  $\text{O}_2$  gas.

**22. (New)** The method of claim 19, wherein said metal source includes at least one said compound selected from the group consisting of  $\text{Hf}(\text{NCH}_3)_2)_4$ ,  $\text{Hf}(\text{N}(\text{C}_2\text{H}_5)(\text{CH}_3))_4$  and  $\text{Hf}(\text{C}_2\text{H}_5)_2)_4$ , and said metal oxide is hafnium oxide.

**23. (New)** The method of claim 19, wherein said metal source includes at least one said compound selected from the group consisting of  $\text{NbCl}_5$ ,  $\text{NbF}_5$  and  $\text{Nb}(\text{N}(\text{C}_2\text{H}_5)_2)_3$ , and said metal oxide is niobium oxide.